

# PSMN5R6-100PS

N-channel 100 V 5.6 mΩ standard level MOSFET in TO220

30 November 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

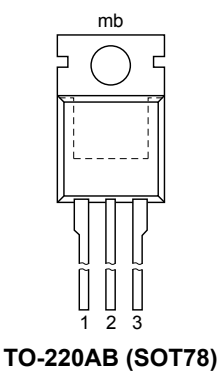
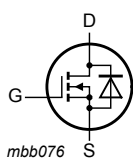
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <a href="#">Fig. 1</a>	[1]	-	-	100	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>		-	-	306	W
<b>Static characteristics</b>							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>		-	4.3	5.6	mΩ
<b>Dynamic characteristics</b>							
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 80 A; V <sub>DS</sub> = 50 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	43	-	nC
Q <sub>G(tot)</sub>	total gate charge			-	141	-	nC
<b>Avalanche Ruggedness</b>							
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 100 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; unclamped		-	-	469	mJ



[1] Continuous current limited by package.

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-220AB (SOT78)</p>	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R6-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN5R6-100PS	PSMN5R6-100PS

## 5. Limiting values

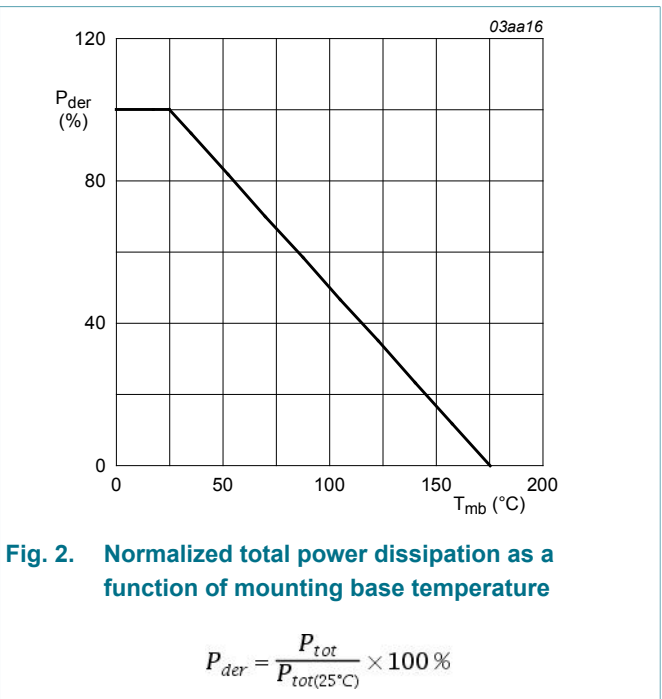
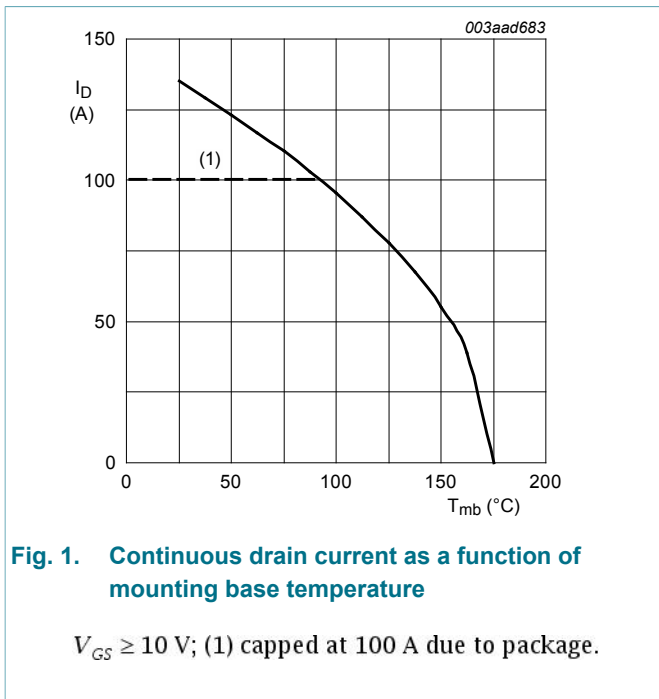
Table 5. Limiting values

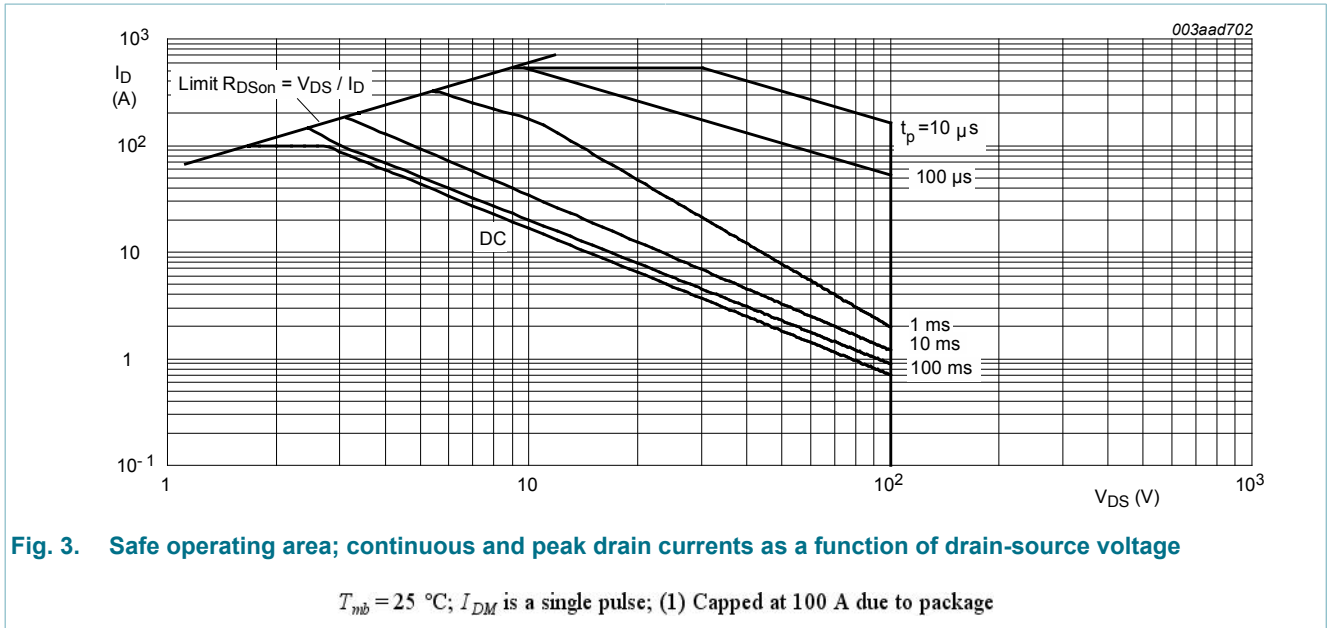
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_j = 100\text{ °C}; \text{Fig. 1}$	-	95	A
		$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 1}$	[1]	100	A

Symbol	Parameter	Conditions	Min	Max	Unit
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10 \mu s$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a>	-	539	A
$P_{tot}$	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>	-	306	W
$T_{stg}$	storage temperature		-55	175	$^\circ\text{C}$
$T_j$	junction temperature		-55	175	$^\circ\text{C}$
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25 \text{ }^\circ\text{C}$	[1]	100	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10 \mu s$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	539	A
<b>Avalanche Ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; $I_D = 100 \text{ A}$ ; $V_{sup} \leq 100 \text{ V}$ ; $R_{GS} = 50 \text{ } \Omega$ ; unclamped	-	469	mJ

[1] Continuous current limited by package.

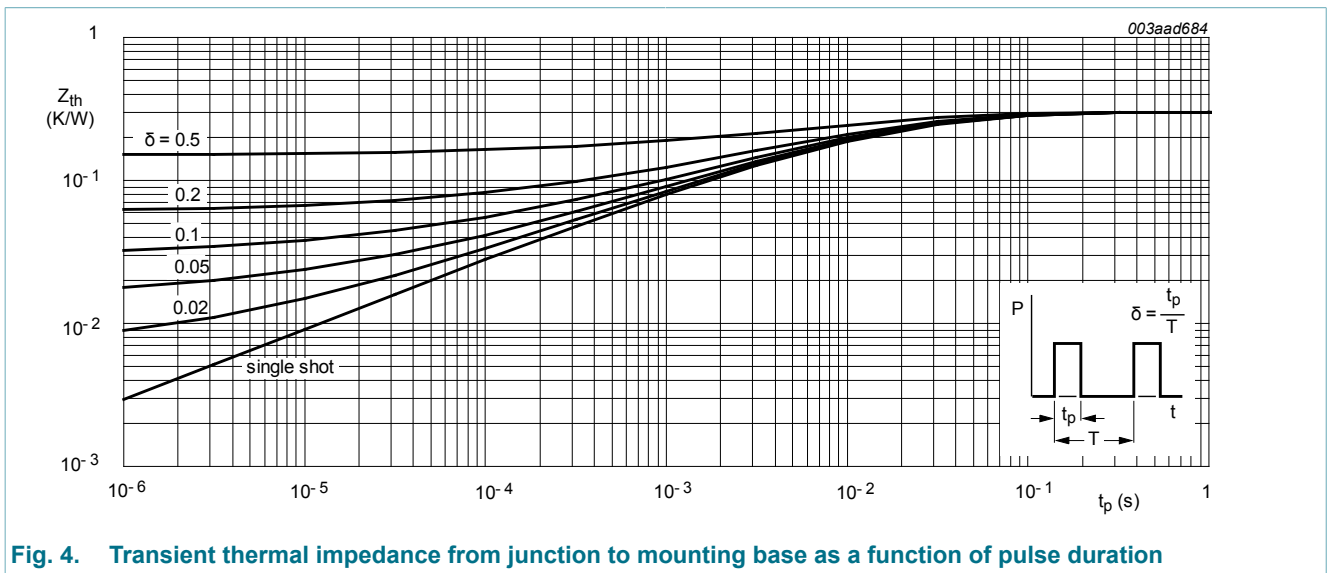




## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	0.3	0.49	K/W



## 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 8; Fig. 9</a>	2	3	4	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ <a href="#">Fig. 9</a>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ <a href="#">Fig. 9</a>	-	-	4.6	V
$I_{DSS}$	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	10	$\mu\text{A}$
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ <a href="#">Fig. 10</a>	-	-	15.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 11; Fig. 12</a>	-	4.3	5.6	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	0.97	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 80 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 13; Fig. 14</a>	-	141	-	nC
$Q_{GS}$	gate-source charge		-	36	-	nC
$Q_{GD}$	gate-drain charge		-	43	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 15; Fig. 16</a>	-	8061	-	pF
$C_{oss}$	output capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 15</a>	-	561	-	pF
$C_{rSS}$	reverse transfer capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 15; Fig. 16</a>	-	330	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 0.6 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 1.5 \text{ } \Omega$	-	31	-	ns
$t_r$	rise time		-	46	-	ns
$t_{d(off)}$	turn-off delay time		-	83	-	ns
$t_f$	fall time		-	34	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 17</a>	-	0.79	1.2	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{rr}$	reverse recovery time	$I_S = 25 \text{ A}$ ; $di_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	67	-	ns
$Q_r$	recovered charge	$V_{DS} = 50 \text{ V}$	-	182	-	nC

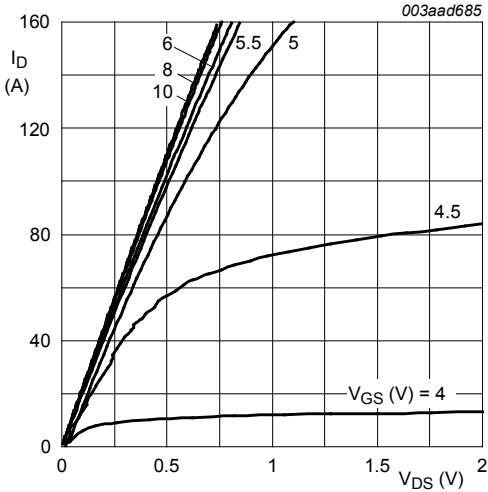


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25 \text{ }^\circ\text{C}$

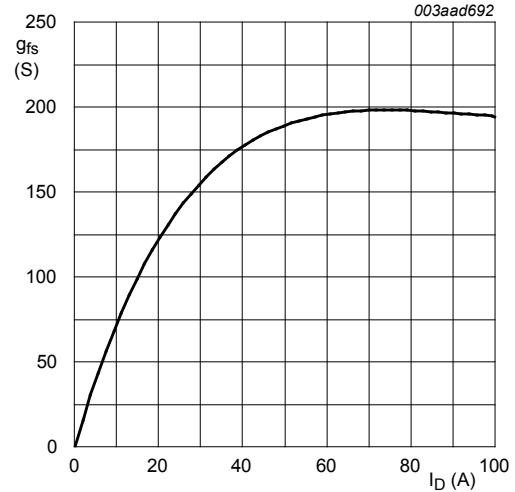


Fig. 6. Forward transconductance as a function of drain current; typical values

$T_j = 25 \text{ }^\circ\text{C}$ ;  $V_{DS} = 25 \text{ V}$

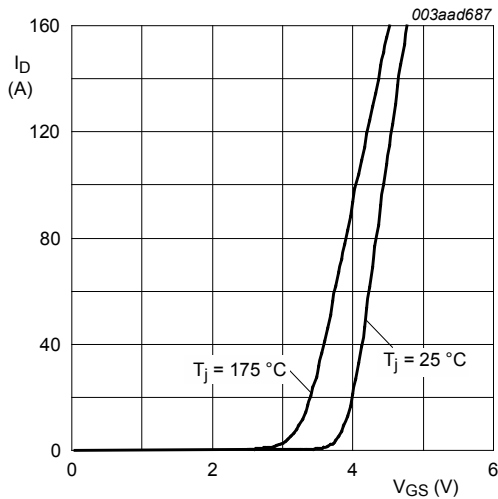


Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} > I_D \times R_{DS(on)}$

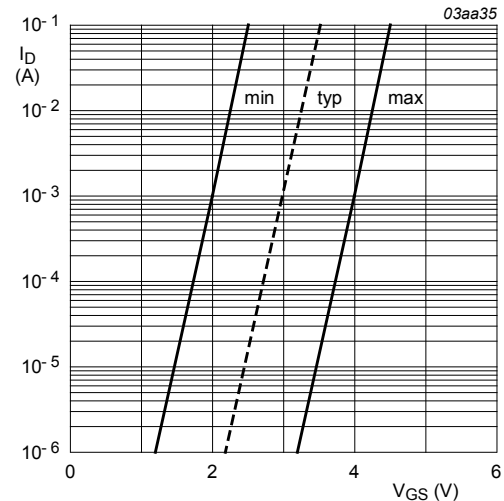
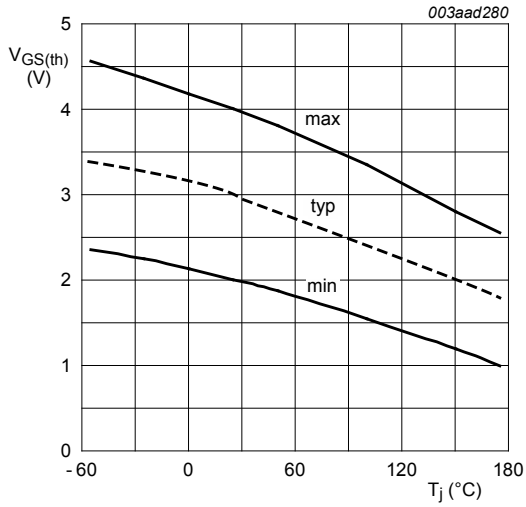


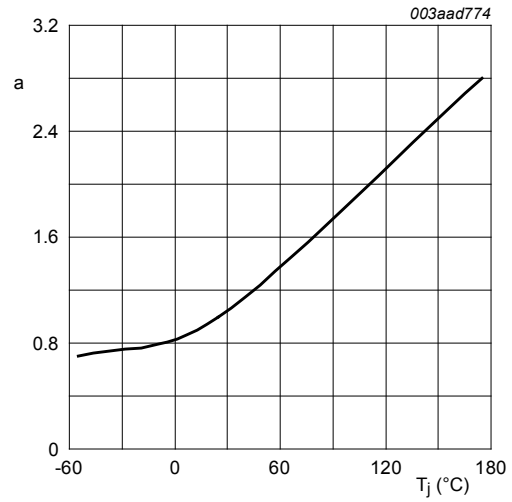
Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25 \text{ }^\circ\text{C}$ ;  $V_{DS} = 5 \text{ V}$



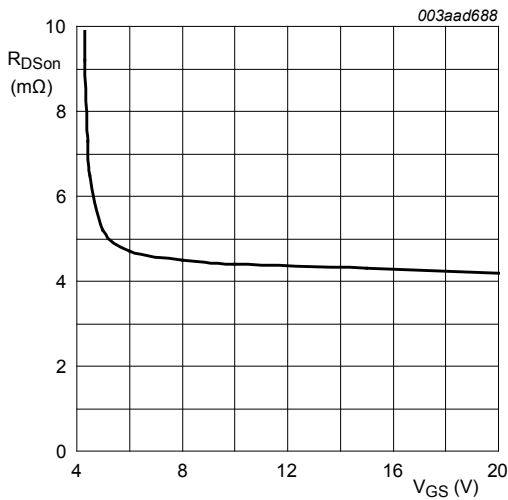
**Fig. 9. Gate-source threshold voltage as a function of junction temperature**

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$



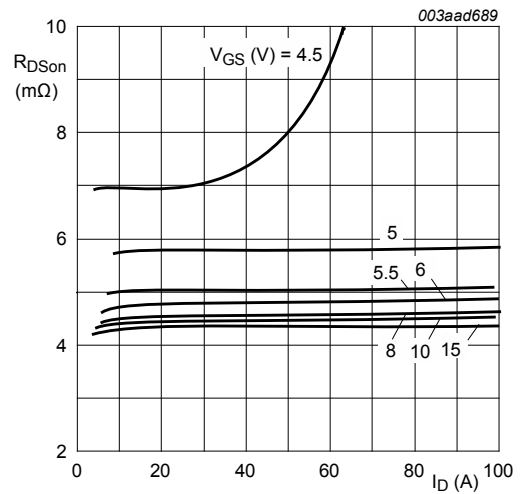
**Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$



**Fig. 11. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$$T_j = 25^\circ\text{C}; I_D = 25 \text{ A}$$



**Fig. 12. Drain-source on-state resistance as a function of drain current; typical values**

$$T_j = 25^\circ\text{C}$$

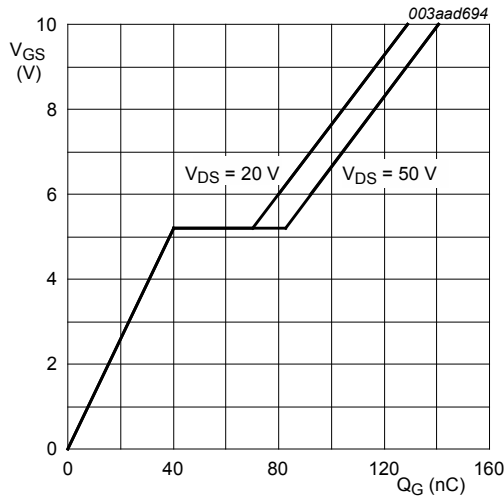


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$T_j = 25\text{ °C}; I_D = 25\text{ A}$

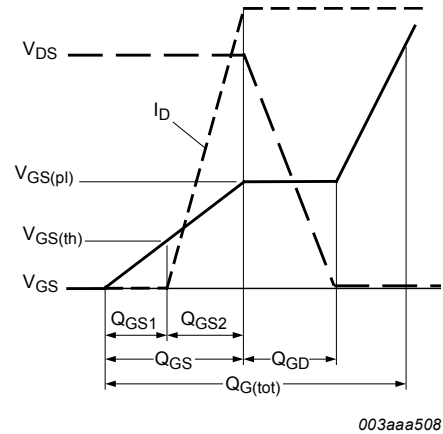


Fig. 14. Gate charge waveform definitions

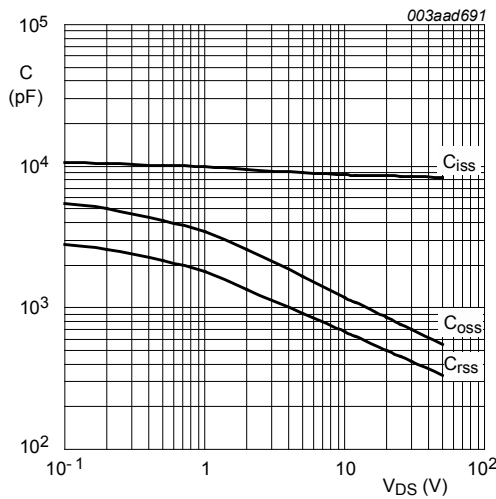


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

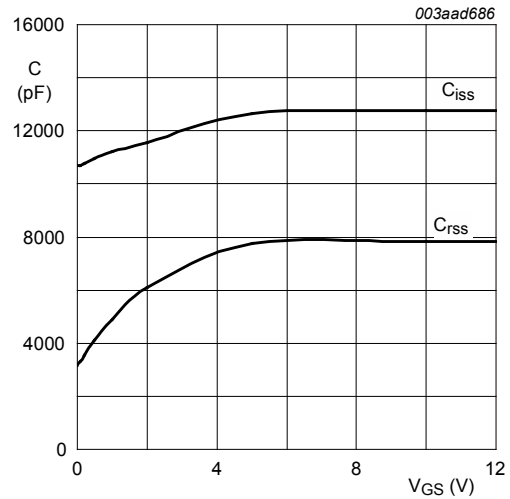


Fig. 16. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

$f = 1\text{ MHz}; V_{DS} = 0\text{ V};$



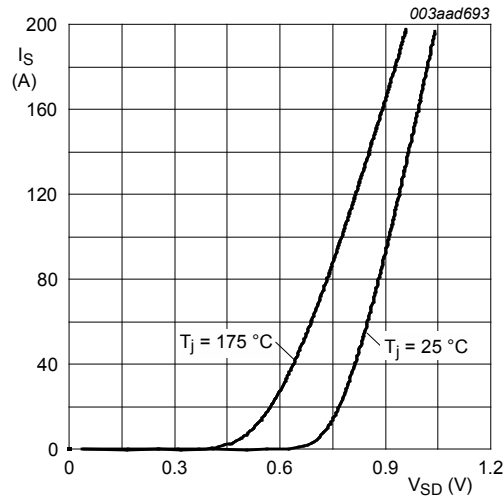


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0 \text{ V}$$

### 8. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



**DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> (1)	L <sub>2</sub> (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

**Notes**

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 18. Package outline TO-220AB (SOT78)

## 9. Legal information

### 9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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